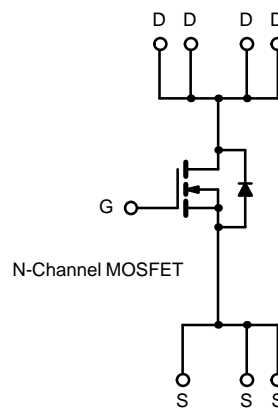
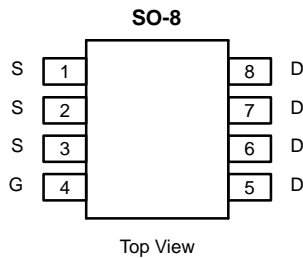




## N-Channel Reduced $Q_g$ , Fast Switching MOSFET

**TrenchFET<sup>®</sup>**  
Power MOSFETs  
**High-Efficiency**  
PWM Optimized

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
30	0.010 @ $V_{GS} = 10$ V	13
	0.0135 @ $V_{GS} = 4.5$ V	11



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	$V_{DS}$	30		V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$			
Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup>	$I_D$	$T_A = 25^\circ\text{C}$	13	9.5	A
		$T_A = 70^\circ\text{C}$	10.5	7.6	
Pulsed Drain Current	$I_{DM}$	$\pm 50$			
Continuous Source Current (Diode Conduction) <sup>a</sup>	$I_S$	2.60	1.40	W	
Maximum Power Dissipation <sup>a</sup>	$P_D$	$T_A = 25^\circ\text{C}$	2.95		1.56
		$T_A = 70^\circ\text{C}$	1.90	1.0	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	$R_{thJA}$	$t \leq 10$ sec	35	42	$^\circ\text{C/W}$
		Steady State	68	80	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	18	23		

Notes

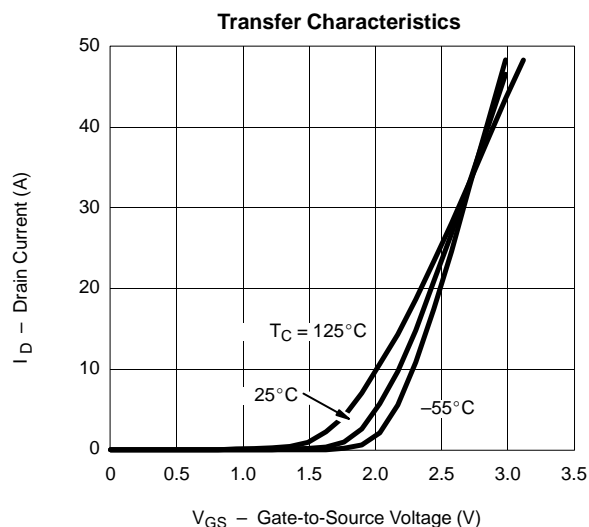
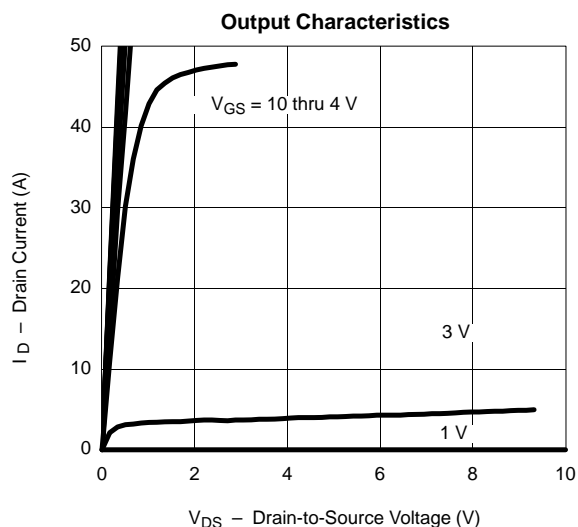
a. Surface Mounted on 1" x 1" FR4 Board.

**MOSFET SPECIFICATIONS ( $T_J = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0.80			V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 70^\circ\text{C}$			5	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			A
Drain-Source On-State Resistance <sup>a</sup>	$r_{DS(on)}$	$V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}$		0.0078	0.010	$\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 11 \text{ A}$		0.0105	0.0135	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15 \text{ V}, I_D = 13 \text{ A}$		38		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.74	1.1	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, V_{GS} = 5.0 \text{ V}, I_D = 13 \text{ A}$		14.5	20	nC
Gate-Source Charge	$Q_{gs}$			3.2		
Gate-Drain Charge	$Q_{gd}$			4.3		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15 \text{ V}, R_L = 15 \Omega$ $I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 6 \Omega$		14	20	ns
Rise Time	$t_r$			5	10	
Turn-Off Delay Time	$t_{d(off)}$			42	80	
Fall Time	$t_f$			18	30	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 2.6 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		40	70	

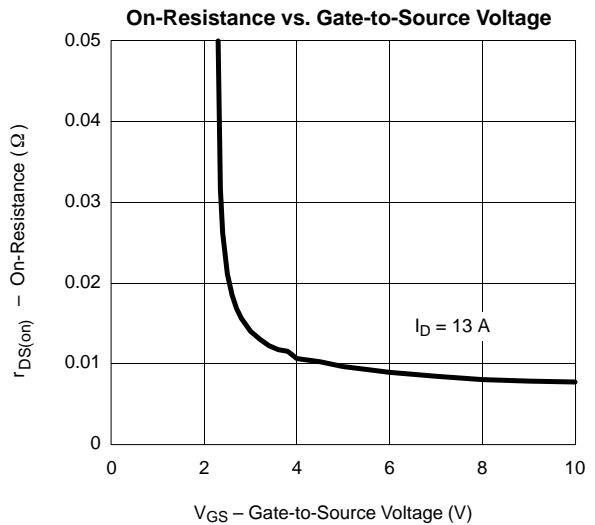
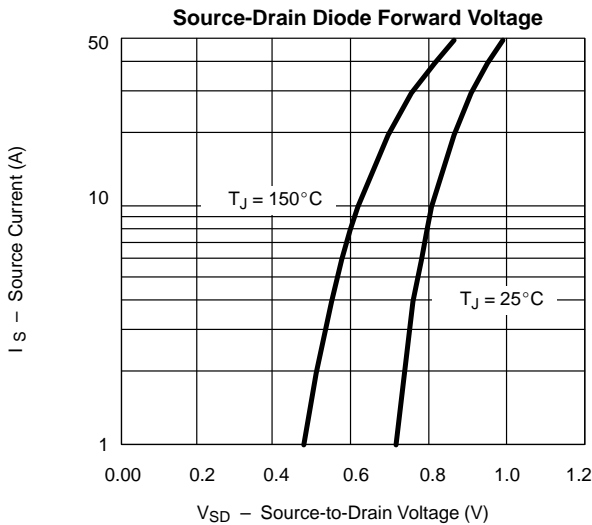
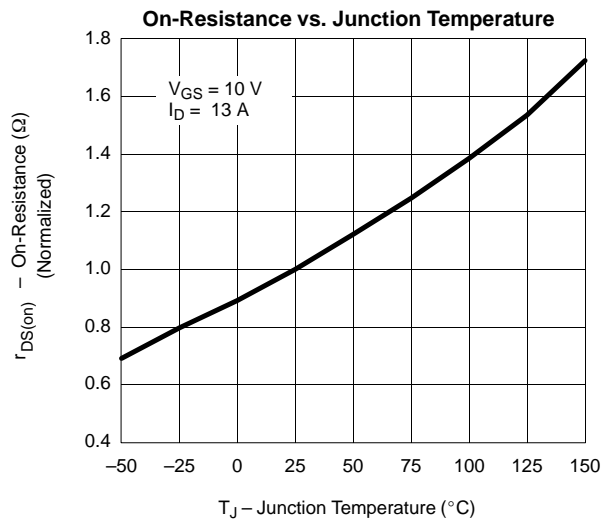
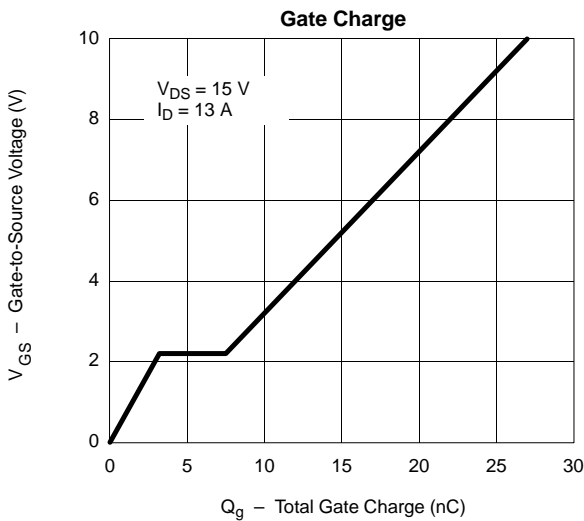
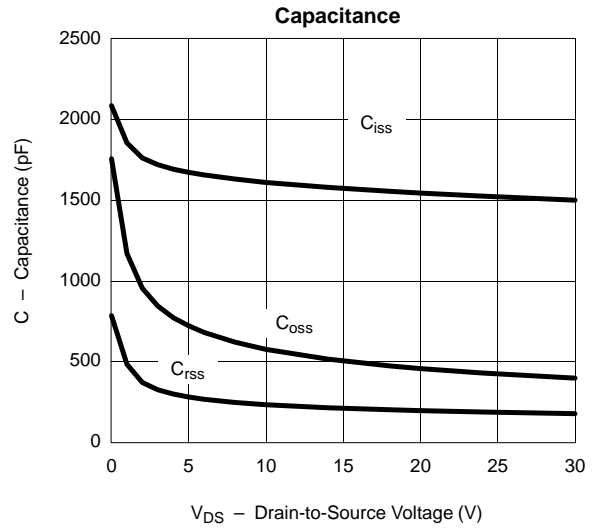
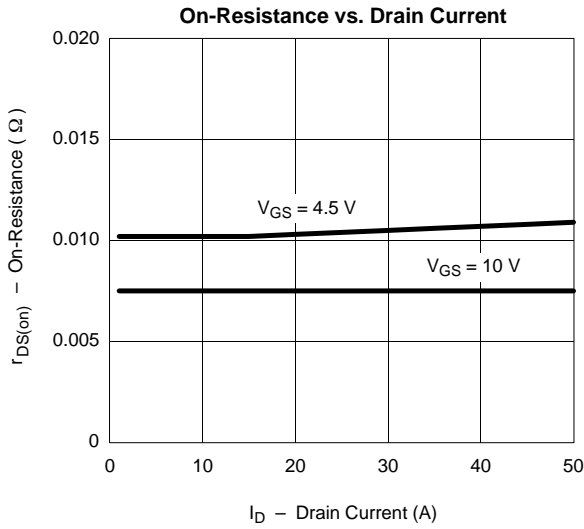
## Notes

- a. Pulse test; pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS ( $25^\circ\text{C}$  UNLESS NOTED)**




**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**





**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)**

